

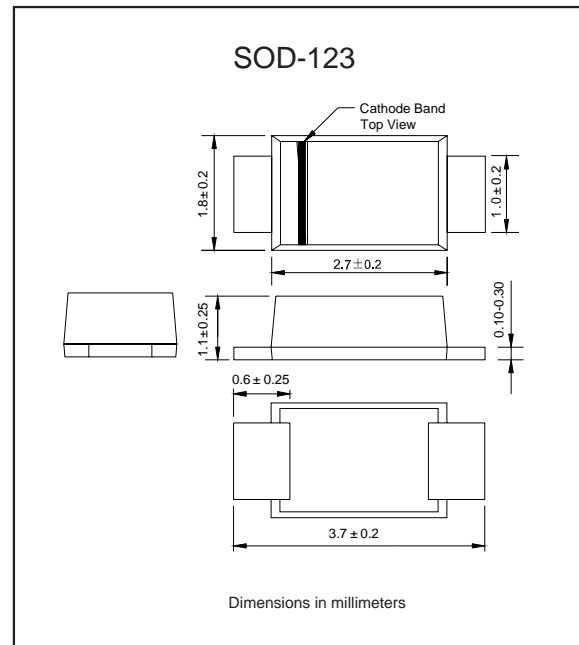
Features

- ◆ Glass passivated device
- ◆ Ideal for surface mounted applications
- ◆ Low reverse leakage
- ◆ Metallurgically bonded construction
- ◆ High temperature soldering guaranteed:
250°C/10 seconds, 0.375" (9.5mm) lead length,
5 lbs. (2.3kg) tension
- ◆ Compliant to RoHS Directive 2011/65/EU
- ◆ Compliant to Halogen-free

Mechanical data

- ◆ **Case:** JEDEC SOD-123 molded plastic body over passivated chip
- ◆ **Terminals:** Plated axial leads, solderable per MIL-STD-750, Method 2026
- ◆ **Polarity:** Color band denotes cathode end
- ◆ **Mounting Position:** Any
- ◆ **Weight:** 0.0007 ounce, 0.02 grams

Package outline



Maximum ratings and Electrical Characteristics (AT $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Forward rectified current	See Fig.2	I_O			1.0	A
Forward surge current	8.3ms single half sine-wave (JEDEC method)	I_{FSM}			25	A
Reverse current	$V_R = V_{RRM}$ $T_A = 25^\circ\text{C}$	I_R			5.0	μA
	$V_R = V_{RRM}$ $T_A = 100^\circ\text{C}$				50	
Thermal resistance	Junction to ambient NOTE 1	$R_{\theta JA}$		180		$^\circ\text{C/W}$
Diode junction capacitance	f=1MHz and applied 4V DC reverse voltage	C_J		20		pF
Storage temperature		T_{STG}	-65		+150	$^\circ\text{C}$

SYMBOLS	V_{RRM}^{*1} (V)	V_{RMS}^{*2} (V)	V_R^{*3} (V)	V_F^{*4} (V)	t_{rr}^{*5} (ns)	Operating temperature T_{Jr} ($^\circ\text{C}$)
DHE1A	50	35	50	1.00	50	
DHE1B	100	70	100			
DHE1D	200	140	200			
DHE1G	400	280	400	1.40	75	
DHE1J	600	420	600	1.70		
DHE1K	800	560	800			
DHE1M	1000	700	1000			

- *1 Repetitive peak reverse voltage
- *2 RMS voltage
- *3 Continuous reverse voltage
- *4 Maximum forward voltage@ $I_F=1.0\text{A}$
- *5 Maximum Reverse recovery time, note 2

Note: 1.P.C.B. mounted with 0.2x0.2" (5.0x5.0mm) copper pad areas
2. Reverse recovery time test condition, $I_F=0.5\text{A}$, $I_R=1.0\text{A}$, $I_{RR}=0.25\text{A}$

Rating and characteristic curves (DHE1A THRU DHE1M)

FIG.1-TYPICAL FORWARD CHARACTERISTICS

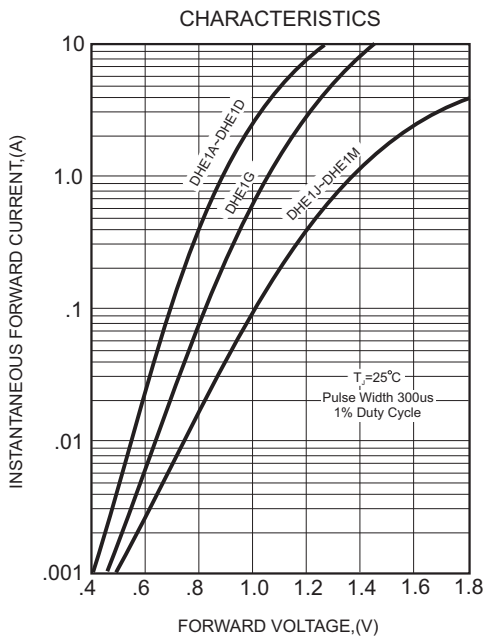


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

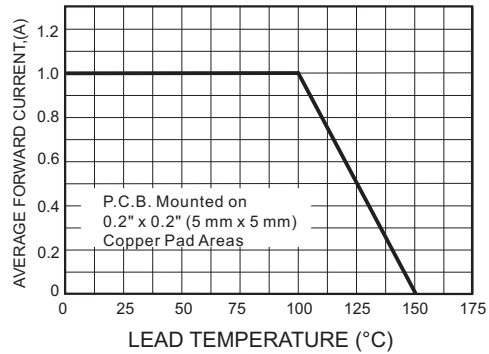


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

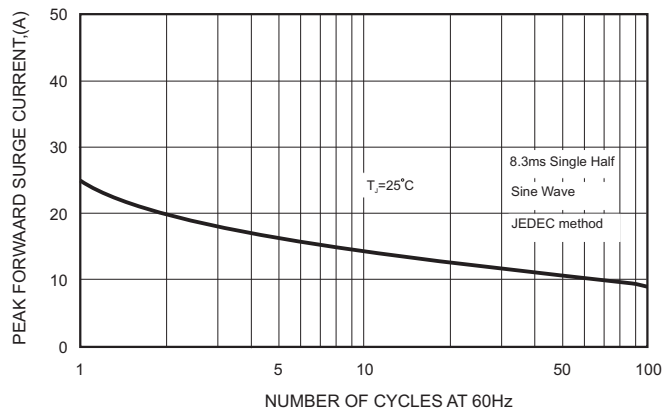
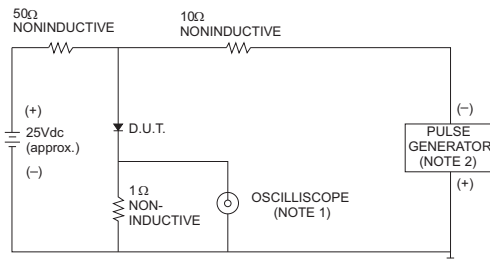


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm.22pF.

2. Rise Time= 10ns max., Source Impedance= 50 ohms.

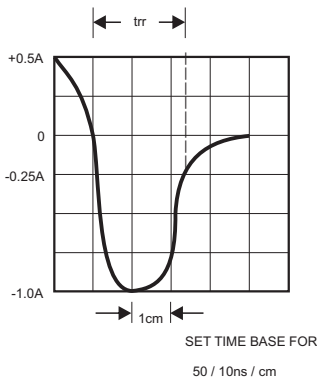
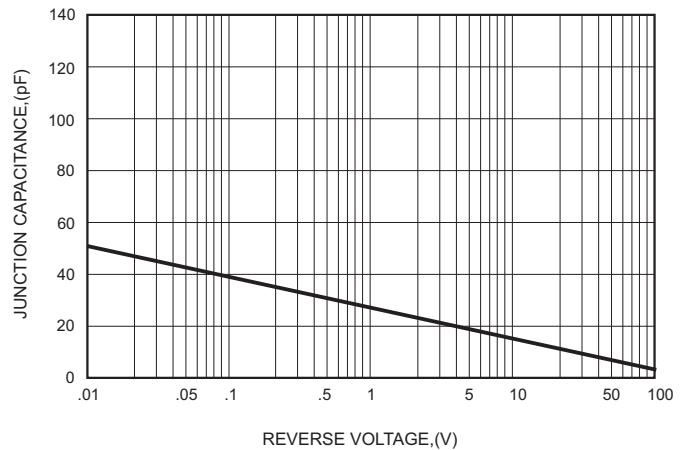




FIG.5-TYPICAL JUNCTION CAPACITANCE



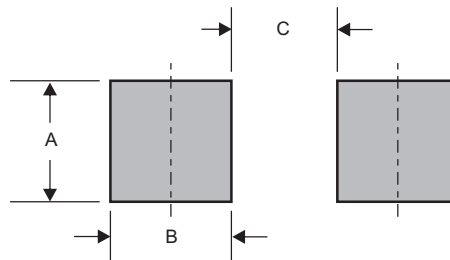
Pinning information

Pin	Simplified outline	Symbol
Pin1 cathode Pin2 anode		

Marking

Type number	Marking code
DHE1A	U1A
DHE1B	U1B
DHE1D	U1D
DHE1G	U1G
DHE1J	U1J
DHE1K	U1K
DHE1M	U1M

Suggested solder pad layout



Dimensions in inches and (millimeters)

PACKAGE	A	B	C
SOD-123	0.075 (1.90)	0.055 (1.40)	0.075 (1.90)

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